NSN 5961-01-333-4341

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View Online at https://aerobasegroup.com/nsn/5961-01-333-4341
Inclosure Material:
Metal
Overall Length:
Between 1.439 inches and 1.573 inches
Overall Height:
Between 0.250 inches and 0.328 inches
Overall Width:
Between 0.990 inches and 1.050 inches
End Application:
Tactical air operations module an/tyq-2 (v) 1
Mounting Facility Quantity:
2
Internal Configuration:
Junction contact
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
To-3
Electrode Internally-electrically Connected To Case:
Collector
Mounting Method:
Unthreaded hole
Features Provided:
Hermetically sealed case and electrostatic sensitive
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
140.0 collector to base voltage/static/emitter open and 120.0 collector to emitter voltage/static/base open and 6.0 emitter to base voltage
static, collector open
Current Rating Per Characteristic:
25.00 amperes source cutoff current and 10.00 amperes source cutoff current
Power Rating Per Characteristic:
200.0 watts small-signal input power, common-collector preset
Transfer Ratio:
12.0 static forward current transfer ratio, common-emitter
Maximum Operating Tempurature Per Measurement Point:
200.0 degrees celsius ambient air
Special Features:
Junction pattern arrangement: pnp
Terminal Type And Quantity:
2 pin and 1 case
Shelf Life:
N/a

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Unit Of Measure:

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